

**N-CHANNEL ENHANCEMENT MODE FIELD EFFECT TRANSISTOR**

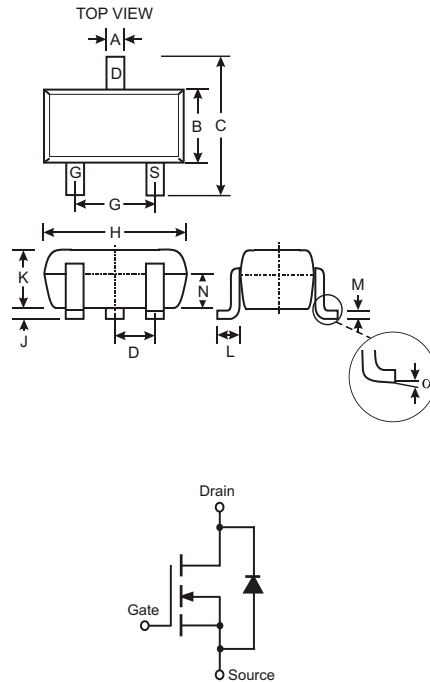
NEW PRODUCT

**Features**

- Low On-Resistance
- Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- Ultra-Small Surface Mount Package

**Mechanical Data**

- Case: SOT-523, Molded Plastic
- Case Material UL Flammability Rating: 94V-0
- Moisture sensitivity: Level 1 per J-STD-020A
- Terminals: Solderable per MIL-STD-202, Method 208
- Terminal Connections: See Diagram
- Marking: 72 (See Page 3)
- Weight: 0.002 grams (approx.)
- Ordering Information, see Page 3



SOT-523			
Dim	Min	Max	Typ
A	0.15	0.30	0.22
B	0.75	0.85	0.80
C	1.45	1.75	1.60
D	—	—	0.50
G	0.90	1.10	1.00
H	1.50	1.70	1.60
J	0.00	0.10	0.05
K	0.60	0.80	0.75
L	0.10	0.30	0.22
M	0.10	0.20	0.12
N	0.45	0.65	0.50
$\alpha$	0°	8°	—
All Dimensions in mm			

**Maximum Ratings** @  $T_A = 25^\circ\text{C}$  unless otherwise specified

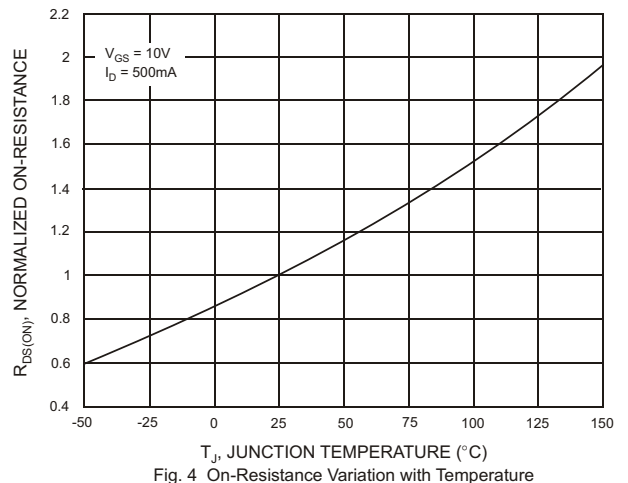
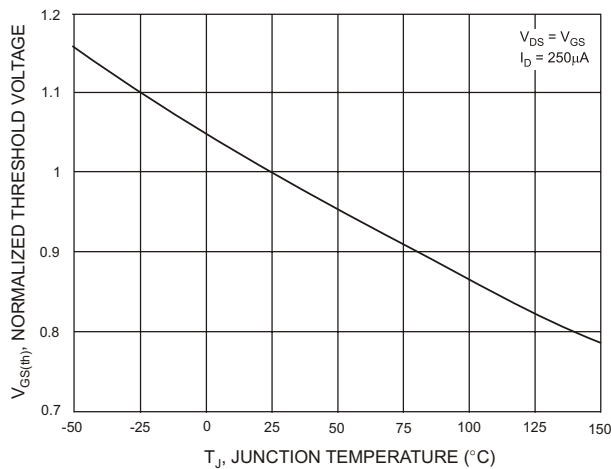
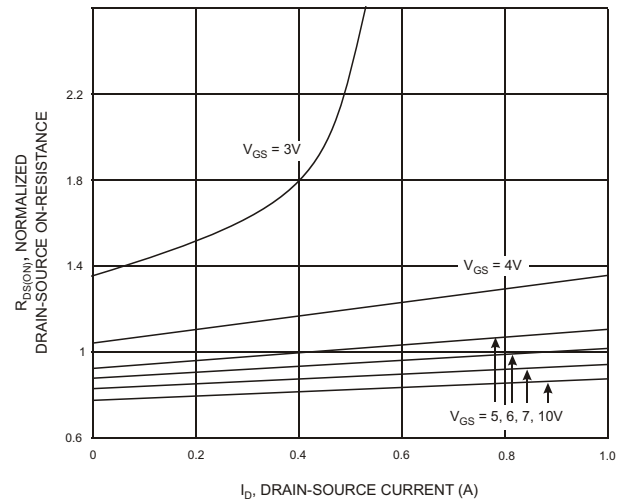
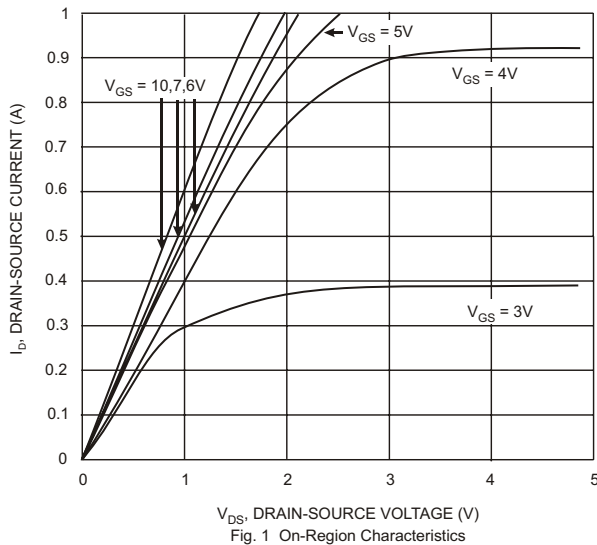
Characteristic	Symbol	Value	Units
Drain-Source Voltage	$V_{DSS}$	60	V
Drain-Gate Voltage $R_{GS} \leq 1.0M\Omega$	$V_{DGR}$	60	V
Gate-Source Voltage	$V_{GSS}$	$\pm 20$	V
Continuous Pulsed		$\pm 40$	
Drain Current	$I_D$	115	mA
Continuous @ 100°C		73	
Pulsed		800	
Total Power Dissipation	$P_d$	150	mW
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	833	°C/W
Operating and Storage Temperature Range	$T_j, T_{STG}$	-55 to +150	°C

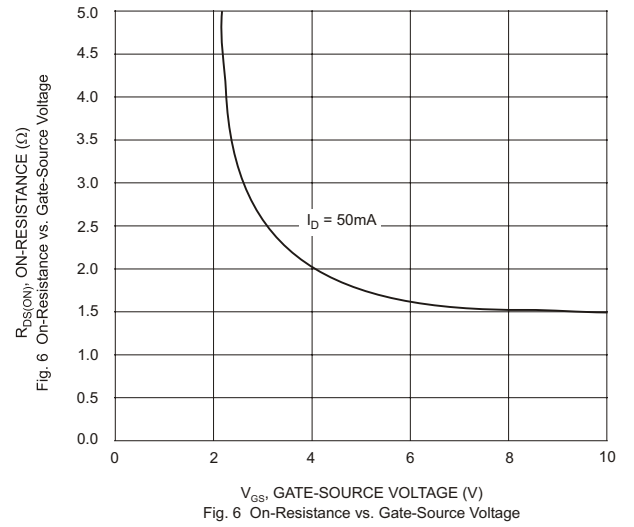
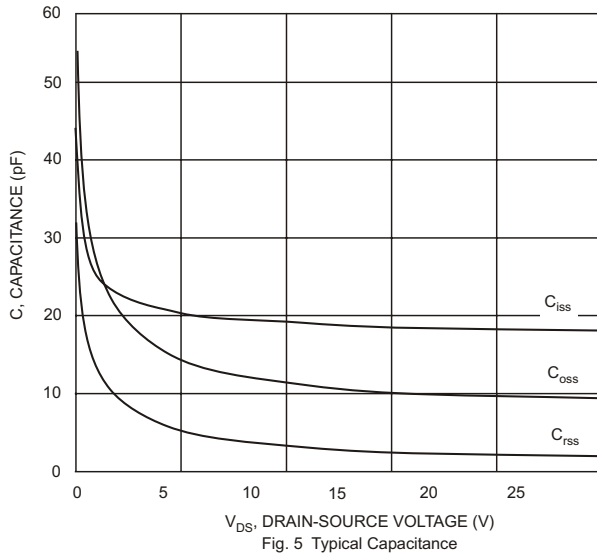
**Electrical Characteristics**

 @  $T_A = 25^\circ\text{C}$  unless otherwise specified

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
<b>OFF CHARACTERISTICS (Note 1)</b>						
Drain-Source Breakdown Voltage	$BV_{DSS}$	60	—	—	V	$V_{GS} = 0V, I_D = 10\mu A$
Zero Gate Voltage Drain Current	$I_{DSS}$	—	—	1.0 500	$\mu A$	$V_{DS} = 60V, V_{GS} = 0V$ @ $T_C = 25^\circ\text{C}$ @ $T_C = 125^\circ\text{C}$
Gate-Body Leakage	$I_{GSS}$	—	—	$\pm 10$	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$
<b>ON CHARACTERISTICS (Note 1)</b>						
Gate Threshold Voltage	$V_{GS(th)}$	1.0	—	2.0	V	$V_{DS} = V_{GS}, I_D = -250\mu A$
Static Drain-Source On-Resistance	$R_{DS(on)}$	—	2.0 4.4	7.5 13.5	$\Omega$	$V_{GS} = 5.0V, I_D = 0.05A$ $V_{GS} = 10V, I_D = 0.5A$
On-State Drain Current	$I_{D(ON)}$	0.5	1.0	—	A	$V_{GS} = 10V, V_{DS} = 7.5V$
Forward Transconductance	$g_{FS}$	80	—	—	mS	$V_{DS} = 10V, I_D = 0.2A$
<b>DYNAMIC CHARACTERISTICS</b>						
Input Capacitance	$C_{iss}$	—	22	50	pF	$V_{DS} = 25V, V_{GS} = 0V$ $f = 1.0\text{MHz}$
Output Capacitance	$C_{oss}$	—	11	25	pF	
Reverse Transfer Capacitance	$C_{rss}$	—	2.0	5.0	pF	
<b>SWITCHING CHARACTERISTICS</b>						
Turn-On Delay Time	$t_{D(ON)}$	—	7.0	20	ns	$V_{DD} = 30V, I_D = 0.2A,$ $R_L = 150\Omega, V_{GEN} = 10V,$ $R_{GEN} = 25\Omega$
Turn-Off Delay Time	$t_{D(OFF)}$	—	11	20	ns	

Note: 1. Short duration test pulse used to minimize self-heating effect.



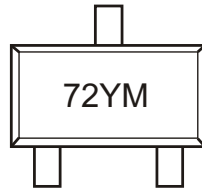


**Ordering Information** (Note 2)

Device	Packaging	Shipping
2N7002T	SOT-523	3000/Tape & Reel

Notes: 2. For Packaging Details, go to our website at <http://www.diodes.com/datasheets/ap02007.pdf>.

**Marking Information**



72 = Product Type Marking Code  
 YM = Date Code Marking  
 Y = Year (ex: N = 2002)  
 M = Month (ex: 9 = September)

Date Code Key

Year	2002	2003	2004	2005	2006	2007	2008	2009
Code	N	P	R	S	T	U	V	W

Month	Jan	Feb	March	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D